

FEATURES

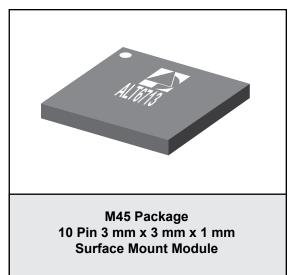
- LTE Compliant
- 4th Generation HELP[™] technology
- High Efficiency (LTE MPR = 0 dB):
 - 35 % @ Pout = +27.5 dBm
 - 18 % @ Pout = +16 dBm
 - 12 % @ Pout = +6 dBm
- Low Quiescent Current: 3 mA
- Low Leakage Current in Shutdown Mode: <5 μA
- Internal Voltage Regulator
- Integrated "daisy chainable" directional coupler with CPLIN and CPLOUT port.
- Optimized for a 50 Ω System
- 1.8 V Control Logic
- RoHS Compliant Package, 260 °C MSL-3

APPLICATIONS

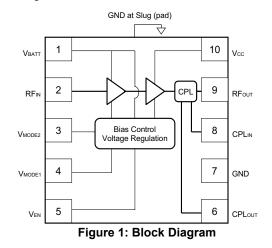
Band 13 & 14 LTE Wireless Devices

PRODUCT DESCRIPTION

The ALT6713 HELP4[™] PA is a 4th generation HELP[™] product for LTE devices operating in UMTS 700 MHz Bands 13 and 14. This PA incorporates ANADIGICS' HELP4[™] technology to deliver exceptional efficiency at low power levels and low quiescent current without the need for external voltage regulators or converters. The device is manufactured using advanced InGaP-

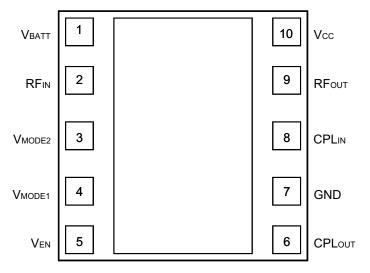


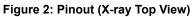
Plus[™] HBT technology offering state-of-the-art reliability, temperature stability, and ruggedness. Three selectable bias modes that optimize efficiency for different output power levels and a shutdown mode with low leakage current increase handset talk and standby time. A "daisy chainable" directional coupler is integrated in the module, thus eliminating the need of an external coupler. The self-contained 3 mm x 3 mm x 1 mm surface mount package incorporates matching networks optimized for output power, efficiency, and linearity in a 50 Ω system.



ALT6713

HELP4[™] UMTS700 (Bands 13 & 14) LTE Linear PAM Data Sheet - Rev 2.7





PIN	NAME	DESCRIPTION
1	VBATT	Battery Voltage
2	RFℕ	RF Input
3	VMODE2	Mode Control Voltage 2
4	VMODE1	Mode Control Voltage 1
5	Ven	PA Enable Voltage
6	CPLout	Coupler Output
7	GND	Ground
8	CPLℕ	Coupler Input
9	RFout	RF Output
10	Vcc	Supply Voltage

Table 1: Pin Description

ELECTRICAL CHARACTERISTICS

PARAMETER	MIN	MAX	UNIT					
Supply Voltage (Vcc)	0	+5	V					
Battery Voltage (VBATT)	0	+6	V					
Control Voltages (VMODE1, VMODE2, VEN)	0	+3.5	V					
RF Input Power (Pℕ)	-	+10	dBm					
Storage Temperature (T _{STG})	-40	+150	°C					

Table 2: Absolute Minimum and Maximum Ratings

Stresses in excess of the absolute ratings may cause permanent damage. Functional operation is not implied under these conditions. Exposure to absolute ratings for extended periods of time may adversely affect reliability.

PARAMETER	MIN	ТҮР	MAX	UNIT	COMMENTS
Operating Frequency (f)	777	-	798	MHz	
Supply Voltage (Vcc)	+3.2	+3.4	+4.35	V	Роит < +27.5 dBm
Enable Voltage (V _{EN})	+1.35 0	+1.8 -	+3.1 +0.5	V	PA "on" PA "shut down"
Mode Control Voltage (VMODE1,VMODE2)	+1.35 0	+1.8 -	+3.1 +0.5	V	Low Bias Mode High Bias Mode
Output Power (UMTS) LTE ⁽¹⁾ (MPR=0), HPM LTE ⁽¹⁾ (MPR=0), MPM LTE ⁽¹⁾ (MPR=0), LPM	27 ⁽²⁾ 15.5 ⁽²⁾ -	27.5 16 6	- -	dBm	TS 36.101 Rel 8 for LTE
Case Temperature (Tc)	-30	-	+90	°C	

Table 3: Operating Ranges

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.

Notes:

(1) LTE waveform characteristics: 10 MHz QPSK, 12 RB.

(2) POUT derated 0.5 dB for 3.2 V operation.

Table 4: Electrical Specifications - LTE Operation (MPR = 0 dB waveform, 10 MHz QPSK, 12 RB)
$(T_c = +25 \text{ °C}, V_{cc} = +3.4 \text{ V}, V_{BATT} = +3.4 \text{ V}, V_{EN} = +1.8 \text{ V}, 50 \Omega \text{ system})$

		7)(7)	мах	UNIT	COMMENTS		
PARAMETER	MIN	TYP			Ролт	VMODE1	V _{MODE2}
Gain	28 14 8	31 17 11	34 20 14	dB	+27.5 dBm +16 dBm +6 dBm	0 V 1.8 V 1.8 V	0 V 0 V 1.8 V
LTE to LTE, E-UTRA	- -	-40 -38 -45	-35 -35 -35	dBc	+27.5 dBm +16 dBm +6 dBm	0 V 1.8 V 1.8 V	0 V 0 V 1.8 V
UTRA ACLR1	- -	-41 -40 -45	-37 -36 -37	dBc	+27.5 dBm +16 dBm +6 dBm	0 V 1.8 V 1.8 V	0 V 0 V 1.8 V
UTRA ACLR2	- -	-64 -60 -66	-40 -40 -40	dBc	+27.5 dBm +16 dBm +6 dBm	0 V 1.8 V 1.8 V	0 V 0 V 1.8 V
Power-Added Efficiency ⁽¹⁾	31 14 9	35 18 12	- - -	%	+27.5 dBm +16 dBm +6 dBm	0 V 1.8 V 1.8 V	0 V 0 V 1.8 V
Quiescent Current (lcq) Low Bias Mode	-	3	4.5	mA	through Vcc pin	1.8 V	1.8 V
Mode Control Current	-	0.08	0.15	mA	through V _{MODE} pins, V _{MODE1,2} = +1.8 V		
Enable Current	-	0.1	0.2	mA	through V _{EN} pin		
BATT Current	-	0.8	1.5	mA	through VBATT pin, VMODE1,2 = +1.8		= +1.8 V
Leakage Current	-	4	10	μA	A VBATT = +4.35 V, VCC = +4.35 V VEN = 0 V, VMODE1,2 = 0 V		.35 V,
Noise Power	- -	-131 -138 -145	- - -	dBm/Hz	746 MHz to 768 MHz GPS Band, 1574 MHz to 1577 MHz ISM Band, 2400 MHz to 2483.5 MHz		
Harmonics 2fo 3fo, 4fo	-	-47 -62	- -	dBc	Pout < +27.5 dBi	m	
Coupling Factor	I	20	-	dB	3		
Directivity	-	19	-	dB			
Daisy Chain Insertion Loss	-	<0.35	-	dB	698 MHz through 2620 MHz Pin 8 through 9, shutdown mode		
Spurious Output Level (all spurious outputs)	-	-	-70	dBc	Pout < +27.5 dB In-band load VS ¹ Out-of-band load Applies over all o	WR < 5:1 I VSWR ∙	< 10:1
Load mismatch stress with no permanent degradation or failure Notes:	8:1	-	-	VSWR	Applies over full	operating	g range

Notes:

(1) ACLR and Efficiency measured at 787 MHz.

APPLICATION INFORMATION

To ensure proper performance, refer to all related Application Notes on the ANADIGICS web site: http://www.anadigics.com

Shutdown Mode

The power amplifier may be placed in a shutdown mode by applying logic low levels (see Operating Ranges table) to the VEN, VMODE1 and VMODE2 voltages.

Bias Modes

The power amplifier may be placed in either Low, Medium or High Bias modes by applying the appropriate logic level (see Operating Ranges table) to the V_{MODE} pins. The Bias Control table below lists the recommended modes of operation for various applications.

Three operating modes are recommended to optimize current consumption. High Bias/High Power operating mode is for Pout levels > 16 dBm. At ~16 dBm - 6 dBm, the PA could be switched to Medium Power Mode. For POUT levels < ~6 dBm, the PA could be switched to Low Power Mode for extremely low current consumption.

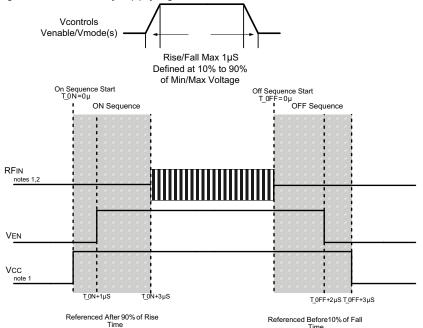


Figure 3: Minimum Recommended ON/OFF Timing Sequence

Notes:

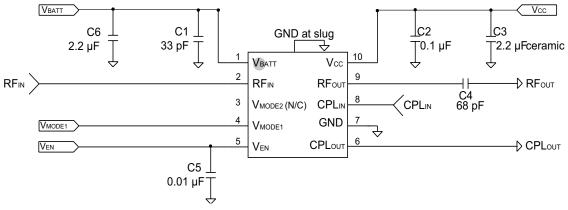
(1) Level may be changed after RF is ON.

(2) RF OFF defined as Pin ≤ -30 dBm.

(3) Simultaneous switching of VMODE and VEN is not recommended

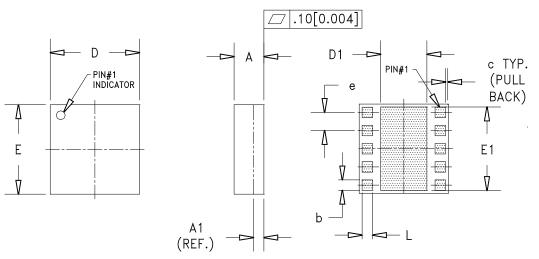
APPLICATION	Pout LEVELS	BIAS MODE	Ven	V MODE1	VMODE2	Vcc	VBATT
Low power (Low Bias Mode)	< +6 dBm	Low	+1.8 V	+1.8 V	+1.8 V	3.2 - 4.35 V	> 3.2 V
Med power (Medium Bias Mode)	> 6 dBm < +16 dBm	Low	+1.8 V	+1.8 V	0 V	3.2 - 4.35 V	> 3.2 V
High power (High Bias Mode)	> +16 dBm	High	+1.8 V	0 V	0 V	3.2 - 4.35 V	> 3.2 V
Shutdown	-	Shutdown	0 V	0 V	0 V	3.2 - 4.35 V	> 3.2 V

Table 5: Dies Control





PACKAGE OUTLINE



SYMBOL	MI	LLIMETER	RS		NOTE		
-0L	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.91	1.03	1.13	0.035	0.041	0.044	-
A1	PLEASE REFER TO LAMINATE CONTROL DRAWING						
b	0.32	0.35	0.40	0.013	0.014	0.016	3
С	-	0.10	-	-	0.004	-	-
D	2.88	3.00	3.12	0.113	0.118	0.123	-
D1	1.45	1.50	1.57	0.057	0.059	0.062	3
Е	2.88	3.00	3.12	0.113	0.118	0.123	-
E1	2.70	2.75	2.85	0.106	0.108	0.112	3
е	0.60				0.024		3
L	0.32	0.35	0.40	0.013	0.014	0.016	3

NOTES:

- 1. CONTROLLING DIMENSIONS: MILLIMETERS
- CONTROLLING DIMENSIONS: MILLIMETERS
 UNLESS SPECIFIED TOLERANCE=±0.076[0.003].

 PADS (INCLUDING CENTER) SHOWN UNIFORM SIZE FOR REFERENCE ONLY. ACTUAL PAD SIZE AND LOCATION WILL VARY WITHIN MIN. AND MAX. DIMENSIONS ACCORDING TO SPECIFIC LAMINATE DESIGN.
 UNLESS SPECIFIED DIMENSIONS ARE SYMMETRICAL ABOUT CENTER LINES SHOWN.
- 5. LAMINATE CONTROL DRAWING SPECIFIED BY PART NUMBER.
- Figure 5: M45 Package Outline 10 Pin 3 mm x 3 mm x 1 mm Surface Mount Module



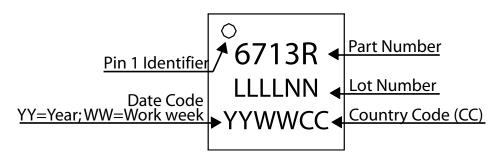
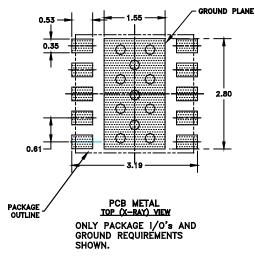


Figure 6: Branding Specification - M45 Package

PCB AND STENCIL DESIGN GUIDELINE



NOTES:

- (1) OUTLINE DRAWING REFERENCE: P8002478_E
- (2) UNLESS SPECIFIED DIMENSIONS ARE SYMMETRICAL ABOUT CENTER LINES SHOWN.
- (3) DIMENSIONS IN MILLIMETERS.
- (4) VIAS SHOWN IN PCB METAL VIEW ARE FOR REFERENCE ONLY. NUMBER & SIZE OF THERMAL VIAS REQUIRED DEPENDENT ON HEAT DISSIPATION REQUIREMENT AND THE PCB PROCESS CAPABILITY.
- (5) RECOMMENDED STENCIL THICKNESS: APPROX. 0.150mm (6 Mils)

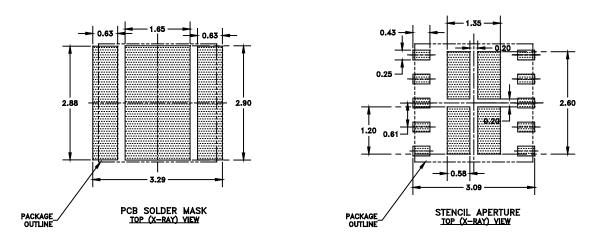
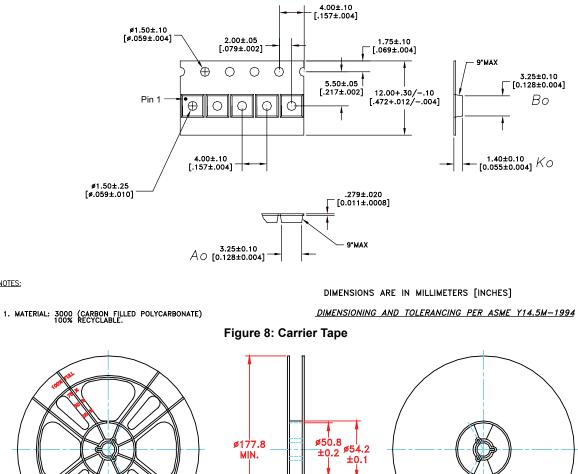


Figure 7: Recommended PCB Layout Information

NOTES:

COMPONENT PACKAGING



-(2X)SLOT 3.0±.1 # (3X)1.78±.25 ø13.0±0.2 ø20.6±0.13 CENTER HOLE DETAIL ENLARGED FOR CLARITY

DIMENSIONS ARE IN MILLIMETERS

-12.4±.1

NOTES:

1. MATERIAL:

SURFACE RESISTIVITY: 1X10⁴TO 1X10⁸ ohms/square

DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994

BLACK CARBON POLYSTYRENE

Figure 9: Reel

ORDERING INFORMATION

ORDER NUMBER TEMPERATURE RANGE		PACKAGE DESCRIPTION	COMPONENT PACKAGING	
ALT6713RM45Q7	-30 °C to +90 °C	RoHS Compliant 10 Pin 3 mm x 3 mm x 1 mm Surface Mount Module	Tape and Reel, 2500 pieces per Reel	
ALT6713RM45P9	-30 °C to +90 °C	RoHS Compliant 10 Pin 3 mm x 3 mm x 1 mm Surface Mount Module	Partial Tape and Reel	

ANADIGICS

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